PCP1302

ON Semiconductor®

P-Channel Power MOSFET –60V, –3A, 266mΩ, Single PCP

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Features

- On-resistance $R_{DS}(on)1=200m\Omega(typ.)$
- 4V drive
- Halogen free compliance
- Protection Diode in

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	VDSS		-60	V
Gate to Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-3	Α
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-12	А
Power Dissipation		Tc=25°C	3.5	W
	PD	When mounted on ceramic substrate (600mm ² ×0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		- 55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Case Steady State	$R_{ heta JC}$	35.7	°C /W
Junction to Ambient When mounted on ceramic substrate (600mm²×0.8mm)	$R_{\theta JA}$	96.1	°C /W

Electrical Characteristics at Ta = 25°C

Dorometer	Cy make al	Con distant	Value			1.1
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _G S=0V	-60			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-60V, V _{GS} =0V			-1	μА
Gate to Source Leakage Current	IGSS	V _{GS} =±20V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transconductance	gFS	V _{DS} =-10V, I _D =-1.5A		3.2		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =-1.5A, V _G S=-10V		200	266	mΩ
	R _{DS} (on)2	I _D =-1A, V _{GS} =-4.5V		245	334	mΩ
	R _{DS} (on)3	I _D =-1A, V _{GS} =-4V		260	374	mΩ
Input Capacitance	Ciss	V _{DS} =-20V, f=1MHz		262		pF
Output Capacitance	Coss			29		pF
Reverse Transfer Capacitance	Crss			19		pF

Continued on next page.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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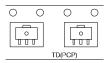
Parameter	Symbol	Constitution of	Value			1.1-34
		Conditions	min	typ	max	Unit
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		5.1		ns
Rise Time	t _r			6.0		ns
Turn-OFF Delay Time	t _d (off)			34		ns
Fall Time	tf			21		ns
Total Gate Charge	Qg	V _{DS} =-30V, V _{GS} =-10V, I _D =-3A		6.4		nC
Gate to Source Charge	Qgs			0.8		nC
Gate to Drain "Miller" Charge	Qgd			1.4		nC
Forward Diode Voltage	V _{SD}	I _S =-3A, V _{GS} =0V		-0.9	-1.5	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Ordering & Package Information

Device	Package	Shipping	note
PCP1302-TD-H	PCP, SC-62 SOT-89, TO-243	1,000 pcs. / reel	Pb-Free And Halogen Free

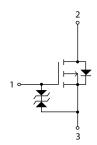
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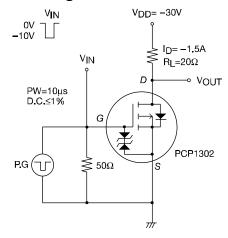
Marking

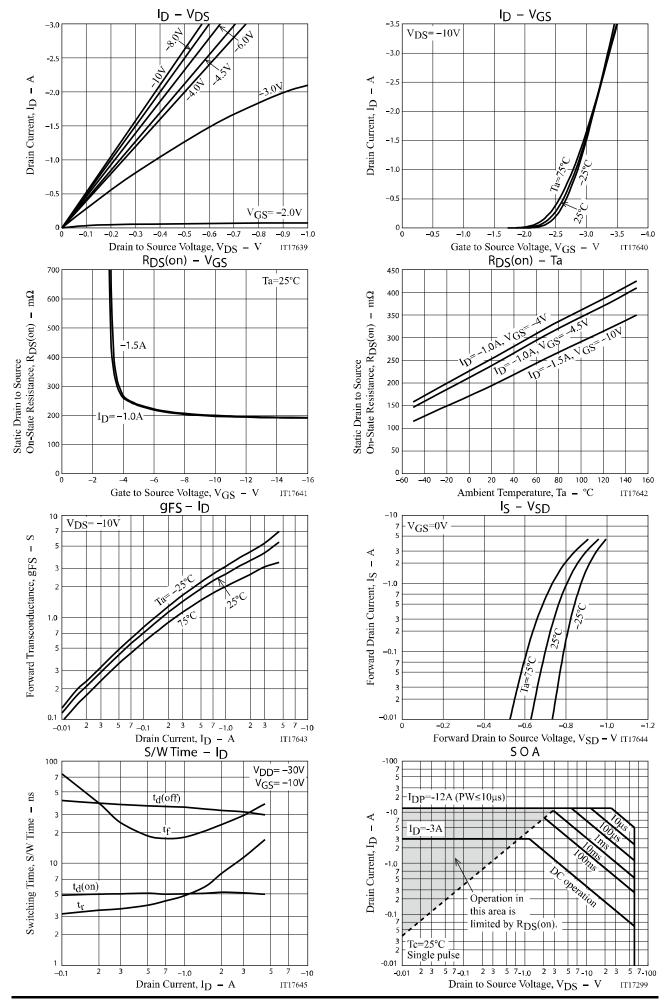


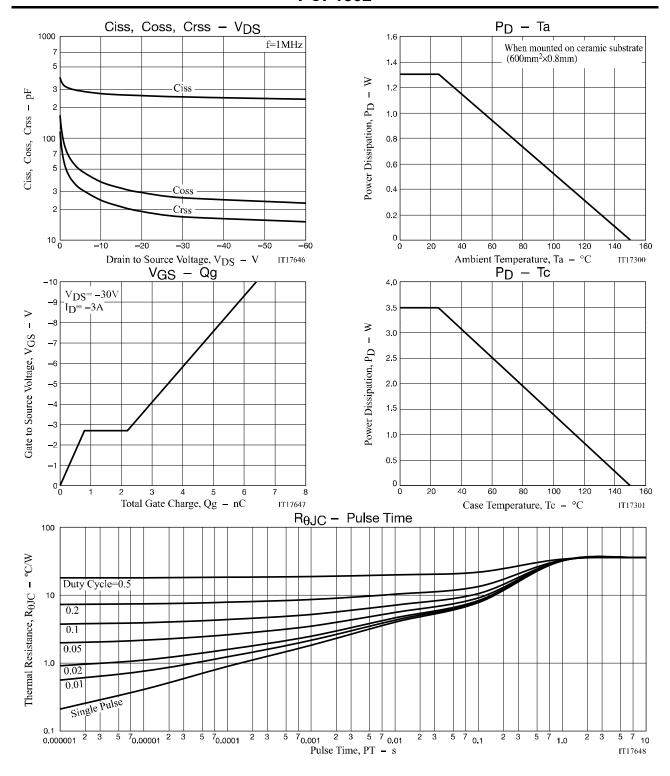
Electrical Connection



Switching Time Test Circuit







Package Dimensions

PCP1302-TD-H

SOT-89/PCP-1

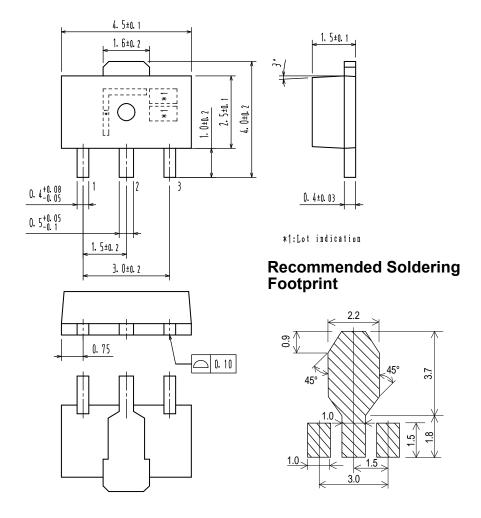
CASE 419AU ISSUE O

Unit: mm

1: Gate

2: Drain

3: Source



Note on usage: Since the PCP1302 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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